

**AMENDMENTS TO THE CLAIMS**

Please amend the claims as follows:

1. (Currently Amended) An integrated circuit comprising:  
a semiconductor substrate;  
an epitaxial layer coupled to the substrate, the epitaxial layer having been coupled to the substrate via a transfer process comprising:  
doping the epitaxial layer with a first quantity of a first ionic material and a second quantity of a second ionic material, wherein the first ionic material comprises helium ions to react with the epitaxial layer at an energy level of approximately 50KeV;  
annealing the epitaxial layer and semiconductor substrate at a first annealing temperature, ~~wherein the first annealing temperature is between approximately 439C and approximately 451C.~~
2. (Original) The integrated circuit of claim 1 wherein the sum of the first quantity of the first ionic material and the second quantity of the second ionic material is no greater than approximately  $2 \times 10^{16} \text{ cm}^{-2}$ .
3. (Canceled)
4. (Currently Amended) The integrated circuit of claim 1 wherein the first annealing temperature is between approximately 419 degrees C and approximately 430 degrees C.

5. (Original) The integrated circuit of claim 4 wherein the process further comprises mechanically separating a donor wafer, comprising the epitaxial layer, from a handle wafer, comprising the semiconductor substrate.

6. (Original) The integrated circuit of claim 2 wherein the second ionic material comprises hydrogen ions to react with the epitaxial layer at an energy level of approximately 40KeV.

7. (Canceled)

8. (Currently Amended) The integrated circuit of claim claim 6 ~~claim 7~~ wherein the first quantity of helium ions is approximately  $1 \times 10^{16} \text{ cm}^{-2}$  and the second quantity of hydrogen ions is approximately  $1 \times 10^{16} \text{ cm}^{-2}$ .

9-35. (Canceled)